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1) page 1, first paragraph, please replace this paragraph with the following:

This application is related to attorney docket number MEG01-001, filed on 01/16/01, serial number 09/760,909, now U.S. Patent 6,426,556, assigned to a common assignee.

IN THE CLAIMS

Please amend the claims as follows.

15. (Amended) A method for forming a metal bump on a semiconductor substrate, comprising the steps of:

providing a semiconductor substrate, said semiconductor substrate having been provided on the surface thereof with a contact pad, said contact pad overlying a layer of dielectric, said layer of dielectric having been deposited over said semiconductor substrate; and

partially removing said contact pad in accordance with a mask of passivation material, said removing having a removal thickness and removal surface area.

19. (Twice Amended) The method of claim 15 wherein said partially removing said contact pad in accordance with a mask of passivation material comprises the steps of:

depositing a layer of passivation material over the surface of said layer of dielectric, including the surface of said contact pad;

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patterning and etching said layer of passivation material, creating an opening in said layer of passivation material having a first diameter, partially exposing the surface of said contact pad over a surface area of said first diameter, said first diameter of said opening created in said layer of passivation material being smaller than a surface area of said contact pad by an amount; and

etching said contact pad, using said patterned layer of passivation material as a mask, creating an opening in said contact pad having a second diameter, partially or completely first removing said contact pad from above the surface of said layer of dielectric, said second diameter of said first opening created in said contact pad being about equal to said first diameter of said opening created in said layer of passivation material.